Schottky Barrier Diode

NSR02L40MX2W

Schottky barrier diodes are optimized for very low forward voltage drop and low leakage current and are used in a wide range of dc-dc converter, clamping and protection applications in portable devices. NSR02L40MX2W in a X2DFNW2 (0402) miniature package enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

Features

- Low Forward Voltage Drop
- Low Reverse Current
- Very High Switching Speed
- Small Body Outline Dimensions: 0.039" x 0.024" (1.00 mm x 0.60 mm)
- Low Body Height: 0.016" (0.40 mm)
- Wettable Flank Package for optimal Automated Optical Inspection (AOI)
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	40	V
Forward Current (DC)	IF	200	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	2.0	Α
ESD Rating: Human Body Model Machine Model	ESD	Class 1C Class A	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

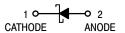
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40 V SCHOTTKY BARRIER DIODE





MARKING DIAGRAM

X2DFNW2 CASE 711BG



XX = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NSR02L40MX2WT5G	X2DFNW2 (Pb-Free)	8000 / Tape & Reel
NSVR02L40MX2WT5G	X2DFNW2 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSR02L40MX2W

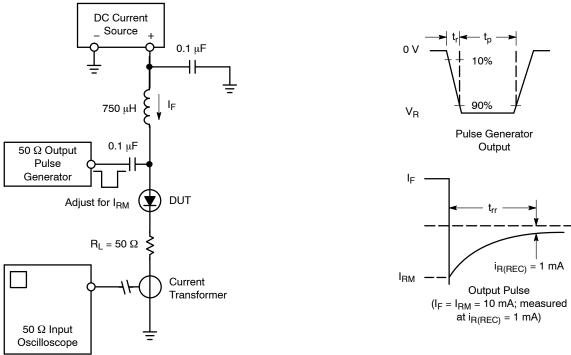
THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Thermal Resistance Junction-to-Ambient (Note 1) Total Power Dissipation @ T _A = 25°C	R _{θJA} P _D			400 300	°C/W mW
Thermal Resistance Junction-to-Ambient (Note 2) Total Power Dissipation @ T _A = 25°C	R _{θJA} P _D			225 425	°C/W mW
Junction and Storage Temperature Range	T _J , T _{stg}			-55 to +150	°C

- Mounted onto a 4 in square FR-4 board 10 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.
 Mounted onto a 4 in square FR-4 board 100 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Leakage (V _R = 25 V) (V _R = 40 V)	I _R		0.03 0.04	0.1 0.5	μА
Forward Voltage (I _F = 1 mA) (I _F = 10 mA) (I _F = 40 mA) (I _F = 100 mA)	V _F		0.32 0.43 0.62	0.38 0.50 0.80 1.20	V
Total Capacitance (V _R = 1.0 V, f = 1 MHz)	СТ		2.0	5.0	pF
Reverse Recovery Time (I _F = I _R = 10 mA, I _R = 1.0 mA)	t _{RR}		1.5	4.0	ns

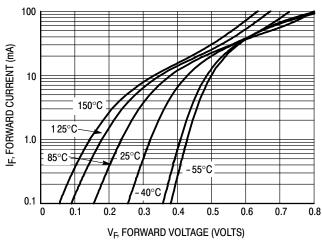


- 1. DC Current Source is adjusted for a Forward Current (I_F) of 10 mA.
- 2. Pulse Generator Output is adjusted for a Peak Reverse Recovery Current $I_{\mbox{RM}}$ of 10 mA.
- Pulse Generator transition time << t_{rr}.
- 4. IR(REC) is measured at 1 mA. Typically 0.1 X I_{RM} or 0.25 X I_{RM} .
- 5. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

NSR02L40MX2W

TYPICAL CHARACTERISTICS



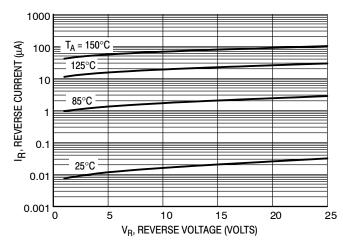


Figure 2. Typical Forward Voltage

Figure 3. Reverse Current versus Reverse Voltage

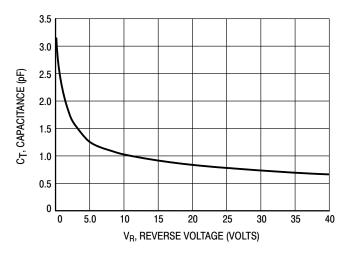


Figure 4. Typical Capacitance



X2DFNW2 1.0x0.6, 0.65PCASE 711BG ISSUE C

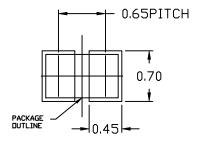
DATE 13 SEP 2019

NOTES:

-D1

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 APPLIES TO THE PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 FROM THE TERMINAL TIP.

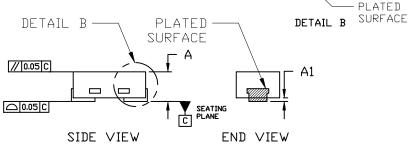
	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	0.34	0.37	0.40	
A1			0.05	
b	0.45	0.50	0.55	
D	0.90	1.00	1.10	
D1			0.05	
Ε	0.50	0.60	0.70	
e	0.65 BSC			
L	0.22 REF			
L1	0.24	0.285	0.34	

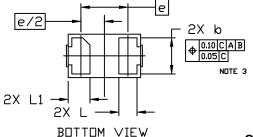


RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

2X 0.05 C PIN 1 REFERENCE TOP VIEW





GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	X2DFNW2 1.0X0.6, 0.65P		PAGE 1 OF 1	

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